

Triacs
Silicon Bidirectional Thyristors

TRIACS
16 AMPERES RMS
600 VOLTS

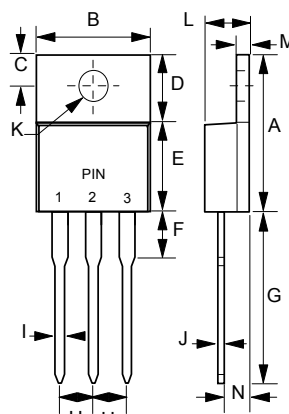
FEATURES

- Minimizes Snubber Networks for Protection
- Blocking Voltage to 600 Volts
- On-State Current Rating of 16 Amperes RMS High Surge Current Capability — 150 Amperes
- Glass Passivated Junctions for Reliability and Uniformity Operational in Three Quadrants, Q1, Q2, and Q3
- Pb Free Package

MECHANICAL DATA

- Case: Molded plastic
- Weight: 0.07 ounces, 2.0 grams

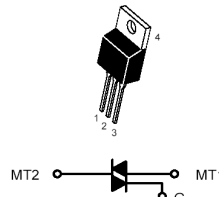
TO-220AB



TO-220AB		
DIM.	MIN.	MAX.
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	8.26	9.28
F	-	6.35
G	12.70	14.73
H	2.29	2.79
I	0.51	1.14
J	0.40	0.67
K	3.53 \varnothing	4.09 \varnothing
L	3.56	4.83
M	1.14	1.40
N	2.03	2.92

All Dimensions in millimeter

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2



MAXIMUM RATINGS (T_J= 25°C unless otherwise noticed)

Rating	Symbol	Value	Unit
Peak Repetitive Off- State Voltage (1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz; Gate Open)	V _{DRM} , V _{RRM}	600	Volts
On-State RMS Current (T _C = +80°C) Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	16	Amp
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 25°C) Preceded and followed by rated current.	I _{TSM}	150	Amps
Circuit Fusing Consideration (t = 8.3 ms)	I ² t	93	A ² s
Peak Gate Power (T _C = +80°C, T _p ≤ 1.0 us)	P _{GM}	20	Watt
Average Gate Power (T _C = +80°C, t=8.3 ms)	P _{G(AV)}	0.5	Watt
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Notice: (1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

REV. 1, May-2007, KTXC21

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance - Junction to Case - Junction to Ambient	R _{thJC} R _{thJA}	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise noted, Electrical apply in both directions)

Characteristics	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (V _D =Rated V _{DRM} , V _{RRM} ; Gate Open)	T _J =25°C	IDRM	----	----	0.01	mA
	T _J =125°C	IRRM	----	----	2.0	

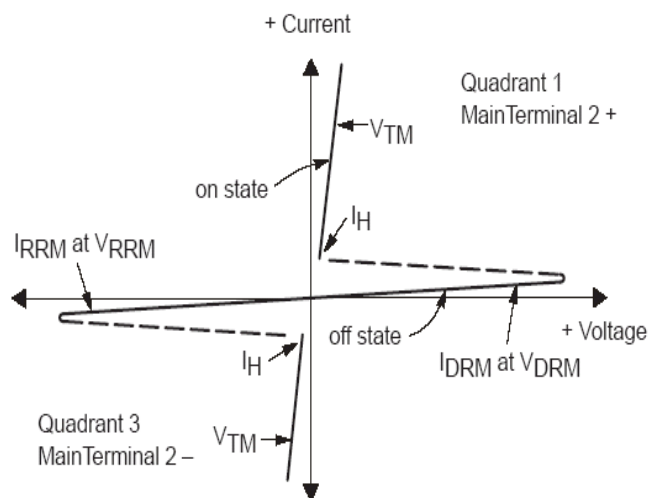
ON CHARACTERISTICS

Peak On-State Voltage (I _{TM} =± 21 A Peak @T _p ≤ 2.0 ms, Duty Cycle ≤ 2%)	V _{TM}	----	1.2	1.6	Volts
Gate Trigger Current (Continuous dc) (V _D = 12Vdc; R _L = 100 Ohms)	I _{GT1}	5.0	12	35	mA
	I _{GT2}	5.0	16	35	
	I _{GT3}	5.0	20	35	
Gate Trigger Voltage (Continuous dc) (V _D = 12 Vdc; R _L =100 Ohms)	V _{GT1}	0.5	0.75	1.5	Volts
	V _{GT2}	0.5	0.72	1.5	
	V _{GT3}	0.5	0.82	1.5	
Holding Current (V _D = 12 V, Initiating Current = ± 150 mA, Gate Open)	I _H	----	20	50	mA
Latching Current (V _D = 12 V, I _G = 35 mA)	I _L	----	25	50	mA
		----	40	80	
		----	24	50	

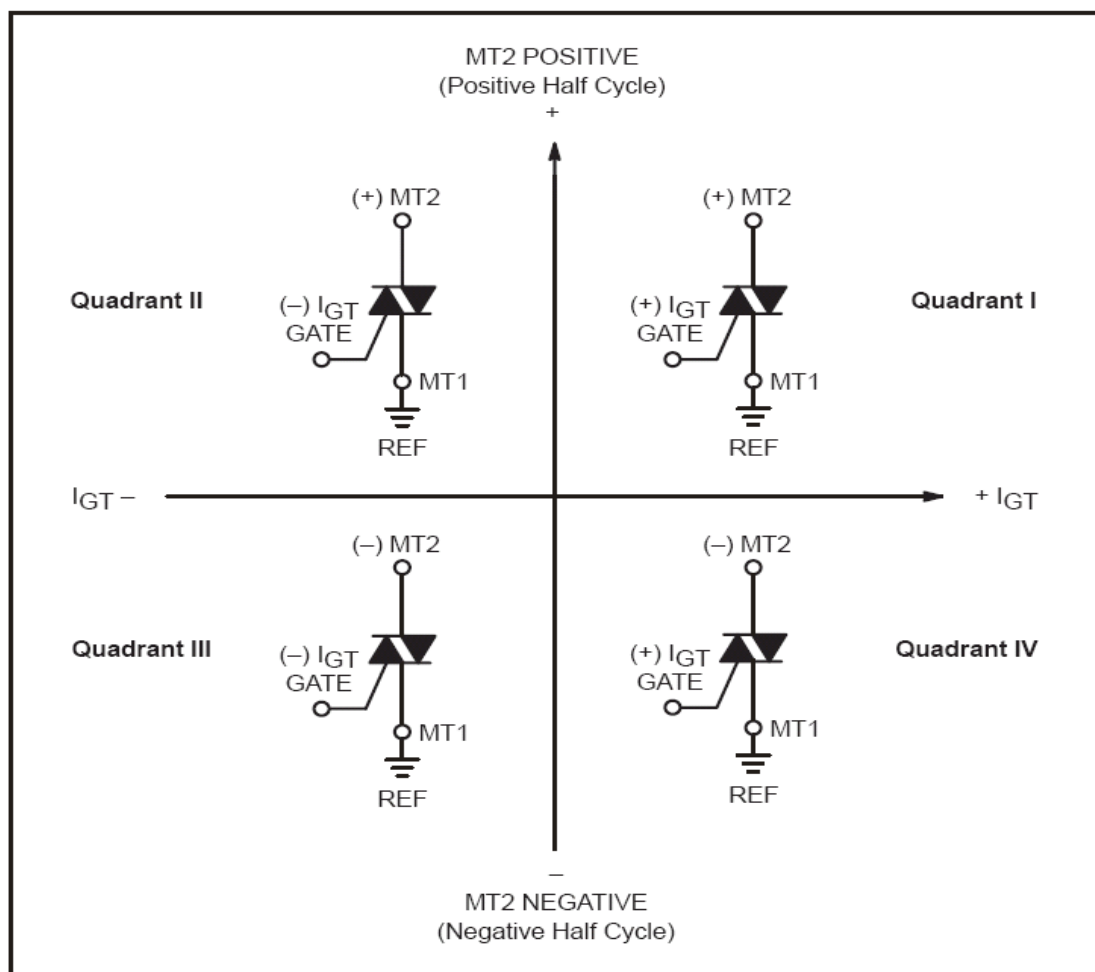
DYNAMIC CHARACTERISTICS

Critical Rate of Change of Commutation Current (V _D = Rated V _{DRM} , I _{TM} = 6.0 A, Commutating dv/dt = 24 V/ms, Gate Unenergized, T _C = 125°C, f = 250 Hz, Snubber: C _L = 10 uf, L _L =40 mH)	di/dt(c)	15	----	----	A/ms
Critical Rate of Rise of Commutation Voltage (V _D = 67% V _{DRM} , Exponential Waveform, T _C = 125°C)	dv/dt	600	----	----	V/us
Repetitive Critical Rate of Rise of On-State Current IPK= 50A, PW=40 us; diG/dt = 200mA/us; f =60Hz	di/dt	---	----	10	A/us

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions



All polarities are referenced to MT1

Whith in -phase signal (using standard AC lines) quadrants I and III are used

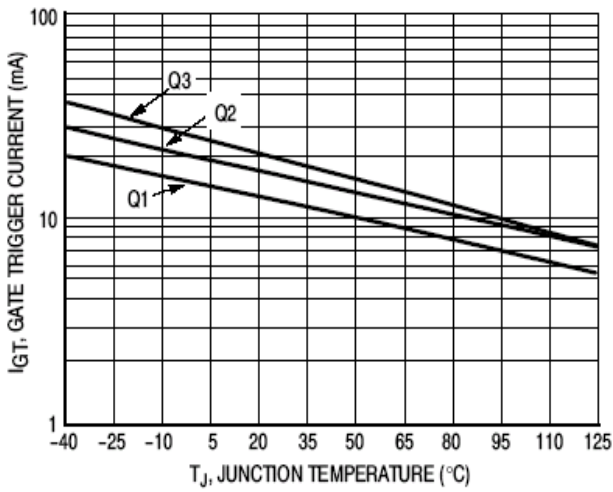


Figure 1. Typical Gate Trigger Current versus Junction Temperature

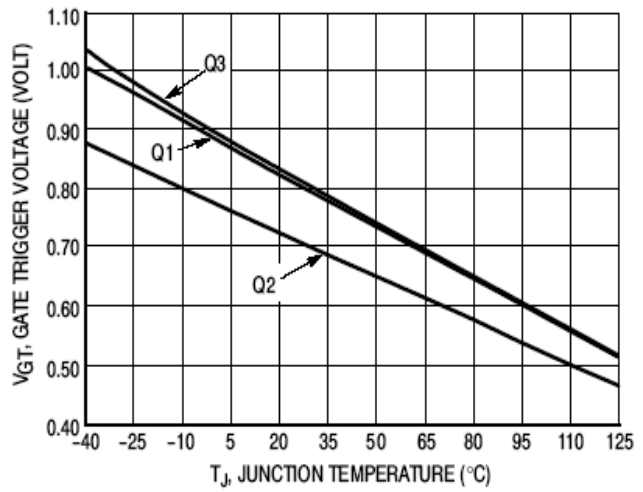


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

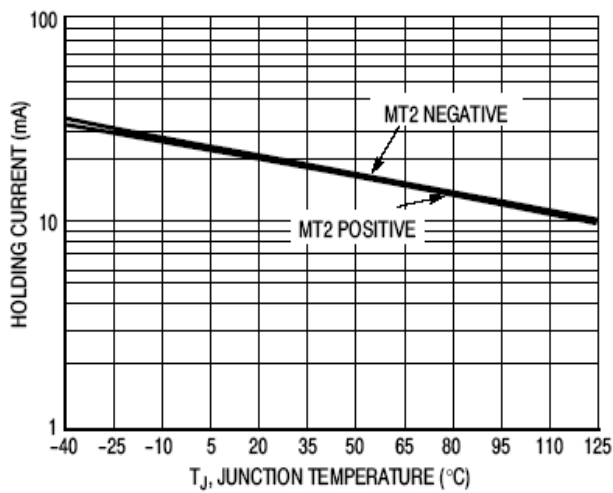


Figure 3. Typical Holding Current versus Junction Temperature

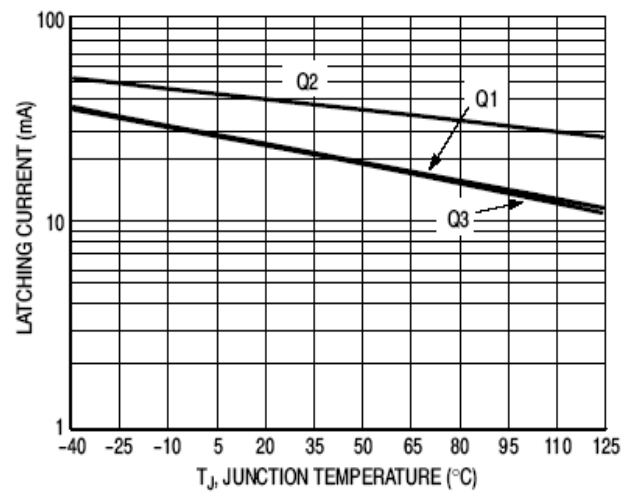


Figure 4. Typical Latching Current versus Junction Temperature

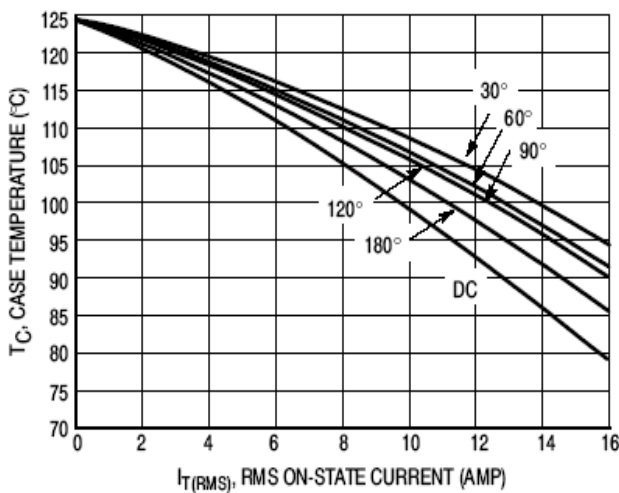


Figure 5. Typical RMS Current Derating

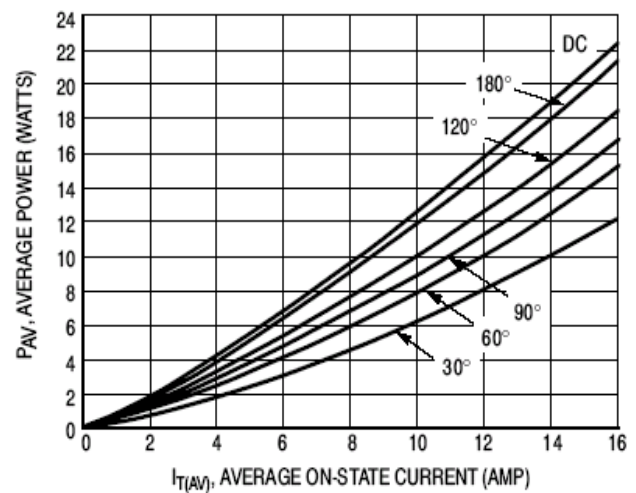


Figure 6. On-State Power Dissipation

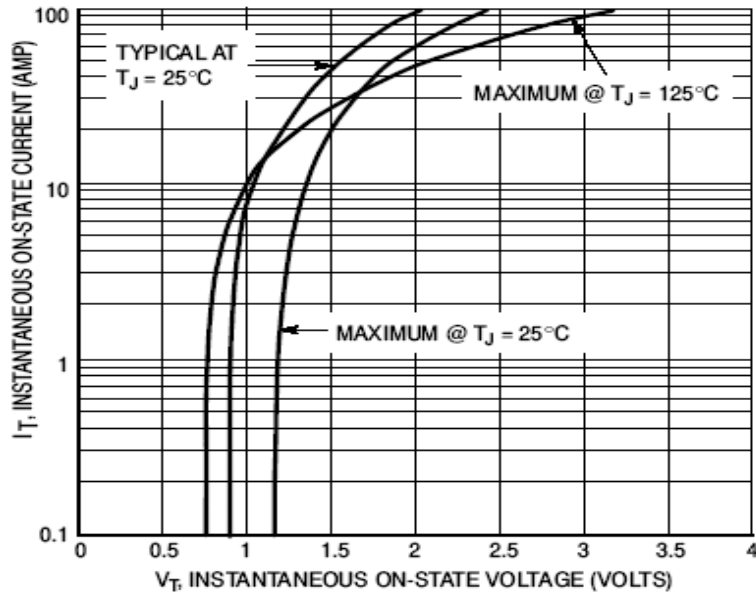


Figure 7. On-State Characteristics

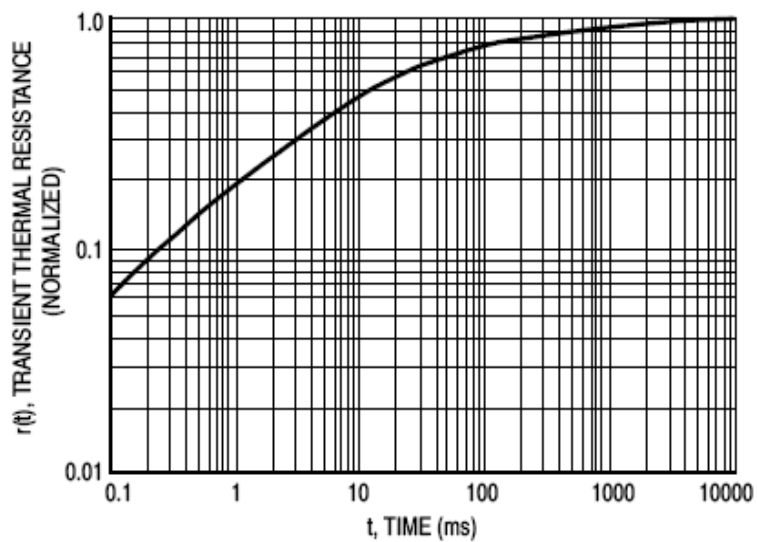


Figure 8. Typical Thermal Response